

# PATENT APPLICATI

Sheet 1 of 2

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LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT

(Use several sheets if necessary)

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## REFERENCE DESIGNATION

Rev 10.00 (PT01449)

#### **U.S. PATENT DOCUMENTS**

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS
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arp	1D	4,760,567	7/1988	Crewe	369	101
Jup	1E	5,402,410	3/1995	Yoshimura et al.	369	275.1
صد	1F	5,557,596	9/1996	Gibson et al.	369	101
	1G					
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	1J					
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#### **FOREIGN PATENT DOCUMENTS**

	DOCUMENT	DATE	NAME		SUB CLASS	TRANSLATION		
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1L								
1M					_			
1N								
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1P								

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JUP	1Q	E. Huber et al., "Laser-Induced Crystallization of Amorphous GeTe: A Time-Resolved Study," Physics Review B, Vol. 36, No. 3, pp. 1595-1604 (July 15, 1987).
Jup	1R	R.T. Howe et al., "Silicon Micromechanics: Sensors and Actuators on a Chip," IEEE Spectrum, pp. 29-35 (July 1990).
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# PATENT APPLICATION

Sheet 2 of 2

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